IRF830

N-channel mosfet transistor
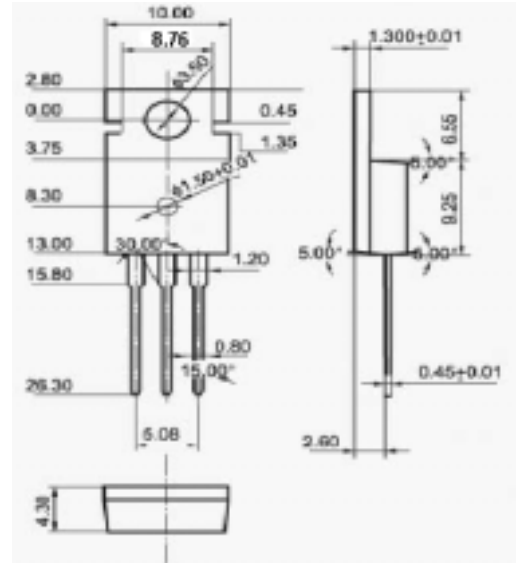

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◆ Features

· With TO-220 package
· Simple drive requirements
· Fast switching
· V_{DSS}=500V; $R_{DS(ON)}$ 1.5 ;I_D=4.5A
· 1.gate 2.drain 3.source

◆ Absolute Maximum Ratings Tc=25

SYMBOL	PARAMETER	RATING	UNIT
V_{DSS}	Drain-source voltage (V_{GS}=0)	500	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain Current-continuous @ T_C=25	4.5	A
P_{tot}	Total Dissipation @ T_C=25	100	W
T_j	Max. Operating Junction temperature	150	
T_{stg}	Storage temperature	-65~150	

TO-220

◆ Electrical Characteristics Tc=25

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS}=0; I_D=0.25mA	500		V
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}= V_{GS}; I_D=0.25mA	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	V_{GS}=10V; I_D=2.7A		1.5	
I_{GSS}	Gate source leakage current	V_{GS}=± 20V; V_{DS}=0		± 100	nA
I_{DSS}	Zero gate voltage drain current	V_{DS}=500V; V_{GS}=0		1.0	uA
V_{SD}	Diode forward voltage	I_F=4.5A; V_{GS}=0		1.6	V